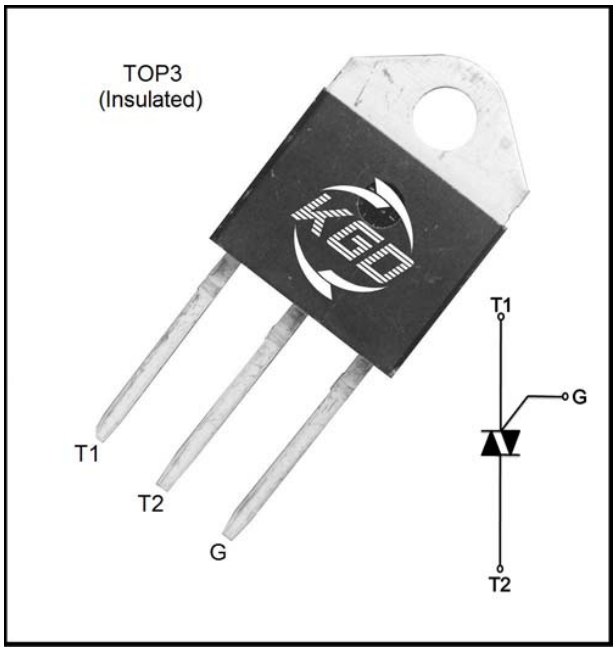
BTA26/BTB26 Series

- **Description:**
  High current density due to double mesa trchnology;
  SIPOS and Glass Passivation.

- **Applications:**
  BTA26 series triacs is suiable for general purpose AC switching.
  They can be used as an ON/OFF function in applications such as static relays,heating regulation,induction motor stating circuits... or for phase contol operation light dimmers,motorspeed controllers.

- **Features:**
  BTA26 Series are 3 Quandrants TRIACS,
  They are specially recommended for use on inductive loads.
  BTA26 are isolated internally,they providesa 2500V RMS isolation voltage from all three terminals to extemal heetsink.
  Blocking voltage to 600/800/1000/1200V
  On-state RMS current to 25A
  Non-repetitive peak on-state current to 250A



- **Absolute Maximum Ratings**

Symbol	Parameter		Conditions	Min	Max	Unit
V_{DRM}	Repetitive peak off-state voltage		T_J=25℃	600	1200	V
V_{RRM}	Repetitive peak Reverse voltage		T_J=25℃	600	1200	V
$I_{T(RMS)}$	RMSon-statecurrent (full sine wave)	TOP3	Tc=100℃	-	25	A
I_{TSM}	Non-repetitive peak On-state current (full cycle, T_J=25℃)		F=50Hz, t=20ms	-	250	A
			F=60Hz, t=16.7ms	-	260	A
I^2t	I^2t Value for fusing		Tp=10ms	-	340	A^2S
di/dt	Rate of rise of on-state current		I_G=2×I_{GT},t_r≤100ns, T_j=125℃	-	50	A/μs
I_{GM}	Peak gate current		t_p=20μs, T_j=125℃	-	4	A
$P_{G(AV)}$	Average gate power			-	1	W
T_{STG}	Storage temperature			-40	150	℃
T_J	Junction temperature			-40	125	℃

Electrical Characteristics

3 Quadrants

Symbol	Conditions	Quadrant		BTA26/BTB26		Unit
				CW	BW	
I_{GT}	V_D=12V,R_L=33Ω	I-II-III	MAX	35	50	mA
V_{GT}		I-II-III	MAX	1.3		V
V_{GD}	V_D=V_{DRM},R_L=3.3KΩ, T_j=125℃	I-II-III	MIN	0.2		V
I_L	I_T=1.2I_{GT}	I-III	MAX	70	80	mA
		II	MAX	80	120	
I_H	I_T=100mA		MAX	50	70	mA
dv/dt	V_{DM}=67%V_{DRM},gate open,T_j=125℃		MIN	500	1000	V/μs
(di/dt)c	Without snubber , T_j=125℃		MIN	13	22	A/ms

4 Quadrants

Symbol	Conditions	Quadrant		BTA26/BTB26		Unit
				C	B	
I_{GT}	V_D=12V,R_L=33Ω	I-II-III	MAX	25	50	mA
		IV		50	100	
V_{GT}		ALL	MAX	1.3		V
V_{GD}	V_D=V_{DRM},R_L=3.3KΩ, T_j=125℃	ALL	MIN	0.2		V
I_L	I_T=1.2I_{GT}	I-III-IV	MAX	70	80	mA
		II	MAX	80	120	mA
I_H	I_T=100mA		MAX	50	70	mA
dv/dt	V_{DM}=67%V_{DRM},gate open,T_j=125℃		MIN	500	1000	V/μs

BTA26/BTB26 Series

● Static Characteristics

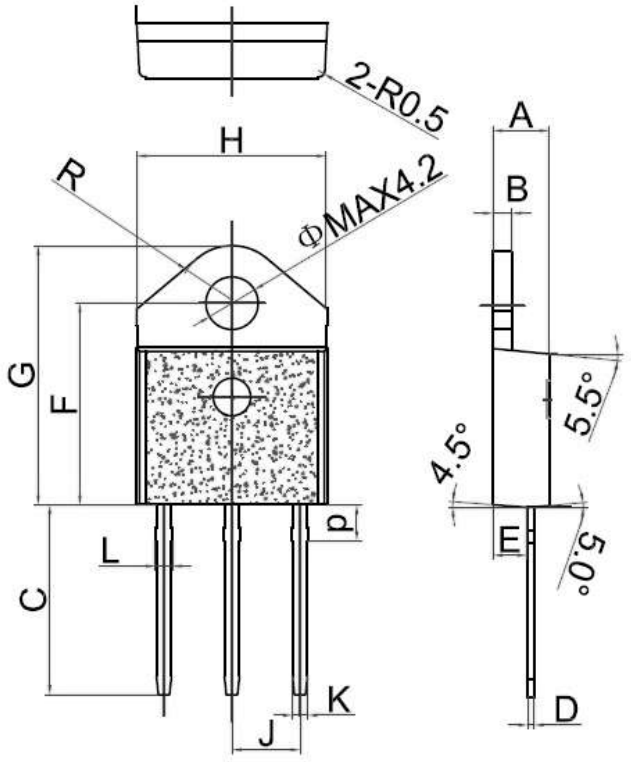
Symbol	Conditions	Quadrant		Value	Unit
V_{TM}	I_T=35A,tp=380μs	T_J=25℃	MAX	1.55	V
I_{DRM} I_{RRM}	V_D=V_{DRM},V_R=V_{RRM}	T_J=25℃	MAX	10	μA
		T_J=125℃	MAX	2	mA

● Thermal Characteristics

Symbol	Parameter		Value	Unit
$R_{th(j-mb)}$	Junction to Case(AC)	TOP3	1.7	℃/W
$R_{th(j-a)}$	Junction to am bient	TOP3	60	℃/W

● Package Outline Dimensions

TOP3(TO-218)



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.4		4.6	0.173		0.181
B	1.45		1.55	0.057		0.061
C	14.35		15.6	0.565		0.614
D	0.5		0.7	0.020		0.028
E	2.7		2.9	0.106		0.114
F	15.8		16.5	0.622		0.650
G	20.4		21.1	0.815		0.831
H	15.1		15.5	0.594		0.610
J	5.4		5.65	0.213		0.222
K	1.2		1.4	0.047		0.055
L	1.35		1.50	0.053		0.059
P	2.8		3.0	0.110		0.118
R		4.6			0.181	